

Ellipse Type Infrared LED

Features:

- * Extra High Radiant Power and Radiant Intensity
- * Low Forward Voltage
- * Suitable For High Pulse Current Operation

Chip Materials:

- * Dice Material : GaAlAs/GaAs
- * Lens Color : Water Clear

Absolute Maximum Rating : (Ta = 25°C)

Symbol	Parameter	Max.	Unit
PD	Power Dissipation Per Chip	200	mW
VR	Reverse Voltage Per Chip	5	V
IF	Forward Current Per Chip	100	mA
IPF	Peak forward current Per Chip (F=1KHZ,duty=0.1)	400	mA
Topt	Operating Temperature Range	-35°C to 85°C	
Tstg	Storage Temperature Range	-35°C to 85°C	

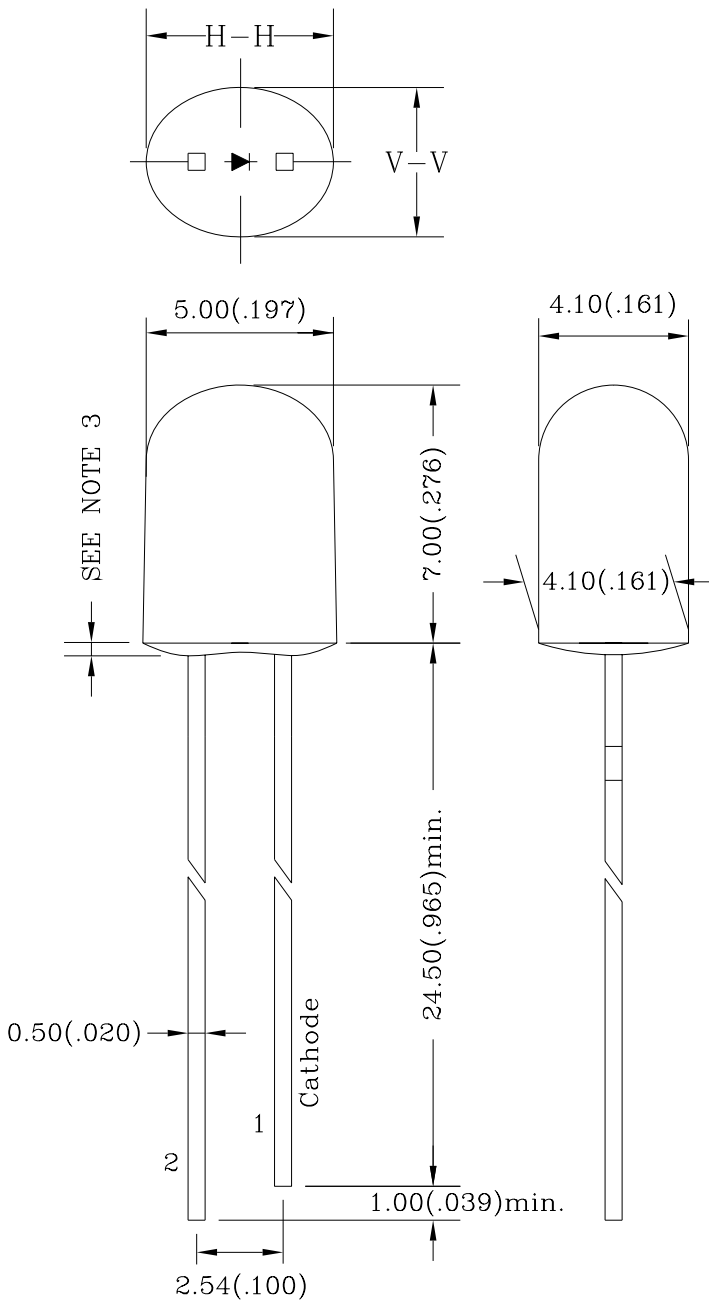
Electro-Optical Characteristics : (Ta = 25°C)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
VF	Forward Voltage	IF = 50mA	1.4		1.6	v
IR	Reverse Current	VR = 5V			10	μA
λP	Peak Emission Wavelength	IF = 50mA		850		nm
2θ1/2	Half Intensity Angle	IF = 50mA		50/20		deg
IE	Radiant Intensity	IF = 50mA	48	60	72	mw/sr
		IF=100mA	100	125	150	

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Package Dimensions

ITEM	MATERIALS
RESIN	Epoxy Resin
LEAD FRAME	Sn Plating iron Alloy



Note:

1. All Dimensions are in millimeters.
2. Tolerance is $\pm 0.25\text{mm}(0.010 \text{ "})$ Unless otherwise specified.
3. Protruded resin under flange is $1.5\text{mm}(0.059 \text{ "})$ max.
4. Lead spacing is measured where the leads emerge from the package.